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L Number	Hits	Search Text	DB	Time stamp
1	32	5676587.pn. 5853604.uref. 5827781.uref.	USPAT;	2003/07/17 12:02
•	J2	0070007.pm 000000 hardh 0027701.ardh	US-PGPUB	
2	8	5733177.uref.	USPAT;	2003/07/17 12:03
		77551771GIGI.	US-PGPUB	2000,07,27 12.00
3	11	(((cmp (chemical near mechanical)) with (copper cu	USPAT;	2003/07/17 12:03
-		conduct\$4 metal))) same (relative near2 (speed velocity))	US-PGPUB	2005/07/17 12:05
4	108	((438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls.	USPAT;	2003/07/17 12:04
7	100	438/691.ccls. 438/692.ccls. 451/41.ccls.) and (relative	US-PGPUB	2005/07/17 12:01
		near2 (speed velocity))) and ((cmp (chemical near	00 1 01 05	
İ		mechanical)) with (copper cu conduct\$4 metal))		
5	3	((438/626.ccls. 438/633.ccls. 438/687.ccls.) and	USPAT;	2003/07/17 12:05
3	,	(438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.))	US-PGPUB	2003/07/17 12:03
		and (relative near2 (speed velocity))	05100	
6	17	(((cmp (chemical near mechanical)) with (copper cu	USPAT;	2003/07/17 12:06
О	1/	conduct\$4 metal))) same ((relative linear) near2 (speed	US-PGPUB	2000/07/17 12.00
		velocity))	0510100	
7	21	(((cmp (chemical near mechanical)) with (copper cu	USPAT:	2003/07/17 12:07
′	2.1	conduct\$4 metal))) same ((rotat\$6 near2 (speed velocity))	US-PGPUB	2005/07/17 12:07
		rpm rpms) same (change decreas\$4 reduc\$5)	00100	
8	3	(((cmp (chemical near mechanical)) with (copper cu	EPO; JPO;	2003/07/17 12:07
0		conduct\$4 metal))) and (relative near2 (speed velocity))	DERWENT;	2003/07/17 12:07
		conduct#4 metaly)) and (relative near 2 (speed velocity))	IBM_TDB	
9	89	(cmp (chemical near mechanical) polish\$4) and ((carrier	USPAT;	2003/07/17 12:08
	0,5	head) same (retain\$4 ring) same membrane same (platen	US-PGPUB	2005/07/17 12:00
		pad) same (pressure psi pa)) and (wafer substrate)	00.00	
10	125	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls.	USPAT;	2003/07/17 12:08
10	123	438/691.ccls. 438/692.ccls. 451/41.ccls.) and (((cmp	US-PGPUB	
		(chemical near mechanical) polish\$4) with (copper cu	00 1 0. 02	
		conduct\$4 metal)) and ((carrier head) same (retain\$4 ring		
		membrane) same (platen pad) same (pressure psi pa)) and		
		(wafer substrate))		
11	126	((cmp (chemical near mechanical) polish\$4) and ((carrier	EPO; JPO;	2003/07/17 12:09
11	120	head) same (retain\$4 ring membrane)) and (platen pad))	DERWENT;	
		and (pressure psi pa copper cu metal conduct\$4)	IBM_TDB	
12	4	(cmp (chemical near mechanical) polish\$4) and (wafer	USPAT;	2003/07/17 12:09
	•	substrate) and ((carrier head) same (platen pad) same (rpm	US-PGPUB	
		adj second))	35 . 3. 35	
13	0	(cmp (chemical near mechanical) polish\$4) and (wafer	USPAT;	2003/07/17 12:09
		substrate) and ((carrier head) same (platen pad) same	US-PGPUB	
		((rpm rotat\$6) near accelerat\$5))		
14	2	(cmp (chemical near mechanical) polish\$4) and (wafer	USPAT;	2003/07/17 12:10
- '	_	substrate)_and ((carrier head) same (platen pad) same	US-PGPUB	
	•	((rpm rotat\$6) with accelerat\$5))		
15	30	(cmp (chemical near mechanical) polish\$4) and (wafer	USPAT;	2003/07/17 12:10
		substrate) and ((carrier head) same (platen pad) same	US-PGPUB	
		accelerat\$5)		